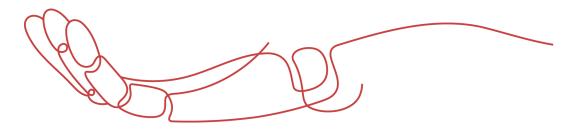


PRODUCT DATA SHEET



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Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.



MMBT2222AW

SURFACE MOUNT SILICON NPN TRANSISTOR



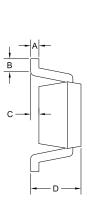
SOT-323

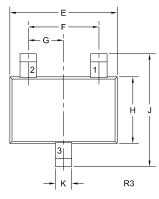
MAXIMUM RATINGS: (T _A =25°C)		SYMBOL		UNITS				
Collector-Base Voltage		V _{CBO}	75	V				
Collector-Emitter Voltage		V _{CEO}	40	V				
Emitter-Base Voltage		V _{EBO}	6.0	V				
Continuous Collector Current		I _C	600	mA				
Power Dissipation		PD	275	mW				
Operating and Storage Junction Temperature		т _Ј , Т _{stg}	-65 to +150	°C				
Thermal Resistance		ΘJA	455	°C/W				
ELECTRICAL CHARACTERISTICS: (T _A =25°C unless otherwise noted)								
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS				
IСВО	V _{CB} =60V		10	nA				
ICBO	V _{CB} =60V, T _A =125°C		10	μA				
ICEV	V_{CE} =60V, V_{EB} =3.0V		10	nA				
I _{EBO}	V _{EB} =3.0V		10	nA				
BVCBO	Ι _C =10μΑ	75		V				
BVCEO	I _C =10mA	40		V				
BVEBO	Ι _Ε =10μΑ	6.0		V				
VCE(SAT)	I _C =150mA, I _B =15mA		0.3	V				
VCE(SAT)	I _C =500mA, I _B =50mA		1.0	V				
V _{BE(SAT)}	I _C =150mA, I _B =15mA	0.6	1.2	V				
V _{BE(SAT)}	I _C =500mA, I _B =50mA		2.0	V				
hFE	V _{CE} =10V, I _C =0.1mA	35						
hFE	V _{CE} =10V, I _C =1.0mA	50						
h _{FE}	V _{CE} =10V, I _C =10mA	75						
hFE	V _{CE} =10V, I _C =150mA	100	300					
hFE	V _{CE} =1.0V, I _C =150mA	50						
h _{FE}	V _{CE} =10V, I _C =500mA	40						
fT	V_{CE} =20V, I _C =20mA, f=100MHz	300		MHz				



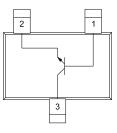
ELECTRIC	AL CHARACTERISTICS - Continued: (T _A =25°C unle	ess otherwise note	ed)	
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
Cob	V _{CB} =10V, I _E =0, f=1.0MHz		8.0	pF
C _{ib}	V _{EB} =0.5V, I _C =0, f=1.0MHz		25	pF
h _{ie}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	2.0	8.0	kΩ
h _{ie}	V _{CE} =10V, I _C =10mA, f=1.0kHz	0.25	1.25	kΩ
	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	0.20		
h _{re}	V _{CE} =10V, I _C =10mA, f=1.0kHz		8.0	x10 ⁻⁴
h _{re}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz		4.0	x10 ⁻⁴
h _{fe}	V _{CE} =10V, I _C =10mA, f=1.0kHz	50	300	
h _{fe}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	75	375	
h _{oe}	V _{CE} =10V, I _C =10mA, f=1.0kHz	5.0	35	μS
h _{oe}	V _{CB} =10V, I _E =20mA, f=31.8MHz	25	200	μS
rb'C _C	V_{CE} =10V, I _C =100µA, R _S =1.0kΩ, f=1.0kHz		150	ps
NF	V_{CC} =30V, V_{BE} =0.5V, I_{C} =150mA, I_{B1} =15mA		4.0	dB
^t d	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA/ _{CC} =30V,		10	ns
t _r	$I_{C}=150$ mA, $I_{B1}=I_{B2}=15$ mA		25	ns
t _s			225	ns
t _f			60	ns

SOT-323 CASE - MECHANICAL OUTLINE





PIN CONFIGURATION



	DIMENSIONS							
	DIMENSIONS							
		INCHES		MILLIMETERS				
5	SYMBOL	MIN	MAX	MIN	MAX			
	А	0.002	0.008	0.05	0.20			
	В	0.004	-	0.10	-			
	С	-	0.004	-	0.10			
	D	0.031	0.043	0.80	1.10			
	Е	0.071	0.087	1.80	2.20			
	F	0.051		1.30				
	G			0.65				
	Н	0.045	0.053	1.15	1.35			
	J	0.079	0.087	2.00	2.20			
	K	0.008	0.016	0.20	0.40			
Se	SOT-323 (REV: R3							

1) Bas

2) Emitter
3) Collector

LEAD CODE:

Ver.1.0



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Ver 10